

PLUS Search Results for S/N 09/451,619, Searched September 12, 2001 (Top 50)

4577215	4618876	4802137	5605853	5940705
5482879	4903097	5212541	5612237	5946240
5879992	5526307	5216268	5625213	5950087
6229176	5760435	5216269	5702965	5972753
5016068	6069381	5289026	5801993	6034892
5295107	6207989	5292681	5814543	6037226
6046086	6239465	5432109	5851880	6093607
4442447	4417264	5447877	5852312	6124168
4513397	4558339	5457061	5858840	6180977
4592130	4590665	5595920	5877525	6188102

Most Frequently Occurring Classifications of Patents Returned
From A Search of 09/451,619 on September 12, 2001

Combined Classifications

12 257/315
12 257/316
10 438/264
9 257/321
9 438/266
7 257/314
6 365/185.18
5 257/317
5 365/185.14
5 438/258
4 257/319
4 365/185.29
4 365/185.33
4 438/257
4 438/265
3 257/320
3 365/185.01
3 365/185.06
3 365/185.1
3 365/185.16
3 365/185.27
3 365/185.28
3 438/201
3 438/267
2 257/318
2 257/324
2 257/330
2 365/185.3
2 365/185.31
2 438/211
2 438/261
2 438/263
2 438/286
2 438/297
2 438/588
2 438/593
2 438/594

12 257/315 (2 OR, 10 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 ..Variable threshold (e.g., floating gate memory device)

257/315 ...With floating gate electrode

12 257/316 (3 OR, 9 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 ..Variable threshold (e.g., floating gate memory device)

257/315 ...With floating gate electrode

257/316With additional contacted control electrode

10 438/264 (6 OR, 4 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS

438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)

438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating gate)

438/264 ...Tunneling insulator

9 257/321 (4 OR, 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 ..Variable threshold (e.g., floating gate memory device)

257/315 ...With floating gate electrode

257/316With additional contacted control electrode

257/321With thin insulator region for charging or discharging floating electrode by quantum mechanical tunneling

9 438/266 (2 OR, 7 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS

438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)

438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating gate)

- 438/266 ...Having additional, nonmemory control
 electrode or channel portion (e.g., for accessing field
 effect transistor structure, etc.)
- 7 257/314 (3 OR, 4 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/213 FIELD EFFECT DEVICE
 257/288 ..Having insulated electrode (e.g., MOSFET, MOS
 diode)
 257/314 ..Variable threshold (e.g., floating gate
 memory device)
- 6 365/185.18 (0 OR, 6 XR)
 Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
 365/185.01 FLOATING GATE
 365/185.18 ..Particular biasing
- 5 257/317 (1 OR, 4 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/213 FIELD EFFECT DEVICE
 257/288 ..Having insulated electrode (e.g., MOSFET, MOS
 diode)
 257/314 ..Variable threshold (e.g., floating gate
 memory device)
 257/315 ...With floating gate electrode
 257/316 With additional contacted control electrode

 257/317 With irregularities on electrode to
 facilitate charging or discharging of floating electrode
- 5 365/185.14 (2 OR, 3 XR)
 Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
 365/185.01 FLOATING GATE
 365/185.05 ..Particular connection
 365/185.14 ..Program gate
- 5 438/258 (2 OR, 3 XR)
 Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
 ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
 ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
 438/197 ..Having insulated gate (e.g., IGFET, MISFET,
 MOSFET, etc.)
 438/257 ..Having additional gate electrode surrounded
 by dielectric (i.e., floating gate)
 438/258 ...Including additional field effect transistor
 (e.g., sense or access transistor, etc.)
- 4 257/319 (3 OR, 1 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/213 FIELD EFFECT DEVICE
 257/288 ..Having insulated electrode (e.g., MOSFET, MOS
 diode)
 257/314 ..Variable threshold (e.g., floating gate
 memory device)